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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Chunlin Liang, et al.

Application No.: 09/517,705

Filed: March 2, 2000

For: COMPLEMENTARY METAL GATE  
ELECTRODE TECHNOLOGY

Examiner: Steven Ho Yin Loke

Art Unit: 2811

Box Non-Fee Amendment  
Assistant Commissioner for Patents  
Washington, D.C. 20231

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TECHNOLOGY CENTER 2800

#12/E  
Amended  
J. McMillan  
9/6/02

AMENDMENT AND RESPONSE TO OFFICE ACTION

In response to the Office Action dated May 21, 2002, Applicants respectfully request entry of the amendments set forth below and consideration of the remarks that follow.

IN THE CLAIMS

Please substitute the following amended claim for the pending claim with the same number:

1. (Three Times Amended) A circuit device comprising:

a first transistor including a first metal gate electrode over a first gate dielectric on a first

area of a semiconductor substrate and having a work function corresponding to the work function

of one of P-type silicon and N-type silicon;

a second transistor complementary to the first transistor including a second metal gate

electrode over a second gate dielectric on a second different area of a semiconductor substrate and

having a work function corresponding to the work function of the other one of P-type silicon and

N-type silicon; and

Sub  
fig. 1  
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